

L Number	Hits	Search Text	DB	Time stamp
-	21	US-3223040-\$.DID. OR US-4793524-\$.DID. OR US-5095938-\$.DID. OR US-5098741-\$.DID. OR US-5195655-\$.DID. OR US-5273851-\$.DID. OR US-5314724-\$.DID. OR US-5356034-\$.DID. OR US-5494712-\$.DID. OR US-5534069-\$.DID. OR US-5593741-\$.DID.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:03
-	27	US-3223040-\$.DID. OR US-4793524-\$.DID. OR US-5095938-\$.DID. OR US-5098741-\$.DID. OR US-5195655-\$.DID. OR US-5273851-\$.DID. OR US-5314724-\$.DID. OR US-5356034-\$.DID. OR US-5494712-\$.DID. OR US-5534069-\$.DID. OR US-5593741-\$.DID.) (US-4894254-\$.DID. OR US-4822632-\$.DID. OR US-4096315-\$.DID.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/01 11:45
-	2	6028015.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/01 11:57
-	37	(US-3223040-\$.DID. OR US-4793524-\$.DID. OR US-5095938-\$.DID. OR US-5098741-\$.DID. OR US-5195655-\$.DID. OR US-5273851-\$.DID. OR US-5314724-\$.DID. OR US-5356034-\$.DID. OR US-5494712-\$.DID. OR US-5534069-\$.DID. OR US-5593741-\$.DID.) (US-4894254-\$.DID. OR US-4822632-\$.DID. OR US-4096315-\$.DID.) 6028015.pn. (US-5876503-\$.DID. OR US-5620524-\$.DID. OR US-5641559-\$.DID. OR US-5738804-\$.DID.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/01 11:57
-	8	US-5876503-\$.DID. OR US-5620524-\$.DID. OR US-5641559-\$.DID. OR US-5730804-\$.DID.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:20
-	37	(US-3223040-\$.DID. OR US-4793524-\$.DID. OR US-5095938-\$.DID. OR US-5098741-\$.DID. OR US-5195655-\$.DID. OR US-5273851-\$.DID. OR US-5314724-\$.DID. OR US-5356034-\$.DID. OR US-5494712-\$.DID. OR US-5534069-\$.DID. OR US-5593741-\$.DID.) (US-4894254-\$.DID. OR US-4822632-\$.DID. OR US-4096315-\$.DID.) 6028015.pn. (US-5876503-\$.DID. OR US-5620524-\$.DID. OR US-5641559-\$.DID. OR US-5730804-\$.DID.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:25
-	6	"2280169"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:04
-	8	"2220869"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:08
-	7	"2111064"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:08
-	13	"2108133"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:10
-	11	"529334"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:10

-	5	"9808249"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:18
-	17	"9401885"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:18
-	2	"5270267".pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:21
-	18	"19654737"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:23
-	37	(US-3223040-\$.DID. OR US-4793524-\$.DID. OR US-5095938-\$.DID. OR US-5098741-\$.DID. OR US-5195655-\$.DID. OR US-5273851-\$.DID. OR US-5314724-\$.DID. OR US-5356034-\$.DID. OR US-5494712-\$.DID. OR US-5534069-\$.DID. OR US-5593741-\$.DID.) (US-4894254-\$.DID. OR US-4822632-\$.DID. OR US-4096315-\$.DID.) 6028015.pn. (US-5876503-\$.DID. OR US-5620524-\$.DID. OR US-5641559-\$.DID. OR US-5730804-\$.DID.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:26
-	39	"5270267".pn. ((US-3223040-\$.DID. OR US-4793524-\$.DID. OR US-5095938-\$.DID. OR US-5098741-\$.DID. OR US-5195655-\$.DID. OR US-5273851-\$.DID. OR US-5314724-\$.DID. OR US-5356034-\$.DID. OR US-5494712-\$.DID. OR US-5534069-\$.DID. OR US-5593741-\$.DID.) (US-4894254-\$.DID. OR US-4822632-\$.DID. OR US-4096315-\$.DID.) 6028015.pn. (US-5876503-\$.DID. OR US-5620524-\$.DID. OR US-5641559-\$.DID. OR US-5730804-\$.DID.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:27
-	2	5786039.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:28
-	41	("5270267".pn. ((US-3223040-\$.DID. OR US-4793524-\$.DID. OR US-5095938-\$.DID. OR US-5098741-\$.DID. OR US-5195655-\$.DID. OR US-5273851-\$.DID. OR US-5314724-\$.DID. OR US-5356034-\$.DID. OR US-5494712-\$.DID. OR US-5534069-\$.DID. OR US-5593741-\$.DID.) (US-4894254-\$.DID. OR US-4822632-\$.DID. OR US-4096315-\$.DID.) 6028015.pn. (US-5876503-\$.DID. OR US-5620524-\$.DID. OR US-5641559-\$.DID. OR US-5730804-\$.DID.))) 5786039.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 10:14
-	14	"254205"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:31
-	13	"726599"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:35
-	24	"212691"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:34

-	15	"826791"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:34
-	2	"9823787"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:37
-	14	"254205"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 17:16
-	12	"761841"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:40
-	44	"519079"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:43
-	18	"19654737"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:45
-	2	"9629576"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:45
-	35	"0051174"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:48
-	2	"200051174"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:46
-	42	"0101472"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:48
-	3	"9943866"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 16:48
-	221	macneil.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 17:16
-	25	(macneil near3 john).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 17:17

-	8	US-5876503-\$.DID. OR US-5620524-\$.DID. OR US-5641559-\$.DID. OR US-5738804-\$.DID.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 17:33
-	4	("5730804" "5786039").pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 17:33
-	6	US-4894254-\$.DID. OR US-4822632-\$.DID. OR US-4096315-\$.DID.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/02 17:38
-	41	("5270267".pn. ((US-3223040-\$.DID. OR US-4793524-\$.DID. OR US-5095938-\$.DID. OR US-5098741-\$.DID. OR US-5195655-\$.DID. OR US-5273851-\$.DID. OR US-5314724-\$.DID. OR US-5356034-\$.DID. OR US-5494712-\$.DID. OR US-5534069-\$.DID. OR US-5593741-\$.DID.) (US-4894254-\$.DID. OR US-4822632-\$.DID. OR US-4096315-\$.DID.) 6028015.pn. (US-5876503-\$.DID. OR US-5620524-\$.DID. OR US-5641559-\$.DID. OR US-5730804-\$.DID.))) 5786039.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 14:28
-	29	("5270267".pn. ((US-3223040-\$.DID. OR US-4793524-\$.DID. OR US-5095938-\$.DID. OR US-5098741-\$.DID. OR US-5195655-\$.DID. OR US-5273851-\$.DID. OR US-5314724-\$.DID. OR US-5356034-\$.DID. OR US-5494712-\$.DID. OR US-5534069-\$.DID. OR US-5593741-\$.DID.) (US-4894254-\$.DID. OR US-4822632-\$.DID. OR US-4096315-\$.DID.) 6028015.pn. (US-5876503-\$.DID. OR US-5620524-\$.DID. OR US-5641559-\$.DID. OR US-5730804-\$.DID.))) 5786039.pn.) and (plasma discharge)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 10:52
-	13	("5270267".pn. ((US-3223040-\$.DID. OR US-4793524-\$.DID. OR US-5095938-\$.DID. OR US-5098741-\$.DID. OR US-5195655-\$.DID. OR US-5273851-\$.DID. OR US-5314724-\$.DID. OR US-5356034-\$.DID. OR US-5494712-\$.DID. OR US-5534069-\$.DID. OR US-5593741-\$.DID.) (US-4894254-\$.DID. OR US-4822632-\$.DID. OR US-4096315-\$.DID.) 6028015.pn. (US-5876503-\$.DID. OR US-5620524-\$.DID. OR US-5641559-\$.DID. OR US-5730804-\$.DID.))) 5786039.pn.) and (plasma discharge) same (heat\$3 hot)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 10:19
-	8	("5270267".pn. ((US-3223040-\$.DID. OR US-4793524-\$.DID. OR US-5095938-\$.DID. OR US-5098741-\$.DID. OR US-5195655-\$.DID. OR US-5273851-\$.DID. OR US-5314724-\$.DID. OR US-5356034-\$.DID. OR US-5494712-\$.DID. OR US-5534069-\$.DID. OR US-5593741-\$.DID.) (US-4894254-\$.DID. OR US-4822632-\$.DID. OR US-4096315-\$.DID.) 6028015.pn. (US-5876503-\$.DID. OR US-5620524-\$.DID. OR US-5641559-\$.DID. OR US-5730804-\$.DID.))) 5786039.pn.) and (plasma discharge) and (heat\$3 hot) near5 (surface substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 10:27
-	4	("5270267".pn. ((US-3223040-\$.DID. OR US-4793524-\$.DID. OR US-5095938-\$.DID. OR US-5098741-\$.DID. OR US-5195655-\$.DID. OR US-5273851-\$.DID. OR US-5314724-\$.DID. OR US-5356034-\$.DID. OR US-5494712-\$.DID. OR US-5534069-\$.DID. OR US-5593741-\$.DID.) (US-4894254-\$.DID. OR US-4822632-\$.DID. OR US-4096315-\$.DID.) 6028015.pn. (US-5876503-\$.DID. OR US-5620524-\$.DID. OR US-5641559-\$.DID. OR US-5730804-\$.DID.))) 5786039.pn.) and (plasma discharge) and (heat\$3 hot) near5 deposit\$8 near5 (film layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 10:34

11	((("5270267".pn. ((US-3223040-\$.DID. OR US-4793524-\$.DID. OR US-5095938-\$.DID. OR US-5098741-\$.DID. OR US-5195655-\$.DID. OR US-5273851-\$.DID. OR US-5314724-\$.DID. OR US-5356034-\$.DID. OR US-5494712-\$.DID. OR US-5534069-\$.DID. OR US-5593741-\$.DID.) (US-4894254-\$.DID. OR US-4822632-\$.DID. OR US-4096315-\$.DID.) 6028015.pn. (US-5876503-\$.DID. OR US-5620524-\$.DID. OR US-5641559-\$.DID. OR US-5730804-\$.DID.))) 5786039.pn.) and (plasma discharge)) and (CVD (chemical near3 vap\$1or near3 deposition)) and (silane organosilicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 10:38
1	((("5270267".pn. ((US-3223040-\$.DID. OR US-4793524-\$.DID. OR US-5095938-\$.DID. OR US-5098741-\$.DID. OR US-5195655-\$.DID. OR US-5273851-\$.DID. OR US-5314724-\$.DID. OR US-5356034-\$.DID. OR US-5494712-\$.DID. OR US-5534069-\$.DID. OR US-5593741-\$.DID.) (US-4894254-\$.DID. OR US-4822632-\$.DID. OR US-4096315-\$.DID.) 6028015.pn. (US-5876503-\$.DID. OR US-5620524-\$.DID. OR US-5641559-\$.DID. OR US-5730804-\$.DID.))) 5786039.pn.) and (plasma discharge)) and (CVD (chemical near3 vap\$1or near3 deposition)) same (silane organosilicon) same (hydrogen near3 peroxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 10:40
108	(CVD (chemical near3 vap\$1or near3 deposition)) same (silane organosilicon tetraethoxysilane) near9 (hydrogen near3 peroxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 10:53
92	((CVD (chemical near3 vap\$1or near3 deposition)) same (silane organosilicon tetraethoxysilane) near9 (hydrogen near3 peroxide)) and (plasma discharge)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 10:52
6	(CVD (chemical near3 vap\$1or near3 deposition)) same (heat\$4 hot) same (silane organosilicon tetraethoxysilane) near9 (hydrogen near3 peroxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 10:53
8	(CVD (chemical near3 vap\$1or near3 deposition)) same (heat\$4 hot) same (silane organosilicon tetraethoxysilane) same (hydrogen near3 peroxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 11:06
51	(CVD (chemical near3 vap\$1or near3 deposition)) same (heat\$4 hot anneal\$5) same (silane organosilicon tetraethoxysilane organosilane) same (hydrogen near3 peroxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 11:09
11	((CVD (chemical near3 vap\$1or near3 deposition)) same (heat\$4 hot anneal\$5) same (silane organosilicon tetraethoxysilane organosilane) same (hydrogen near3 peroxide)) and (plasma corona discharge) near9 treat\$9	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 11:09
131	(CVD (chemical near3 vap\$1or near3 deposition)) same (silane organosilicon tetraethoxysilane organosilane) same (hydrogen near3 peroxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 11:09
6	((CVD (chemical near3 vap\$1or near3 deposition)) same (silane organosilicon tetraethoxysilane organosilane) same (hydrogen near3 peroxide)) and (plasma corona discharge) near9 treat\$9 same (heat\$4 hot anneal\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 11:31
5	"10294311"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 11:35

-	25	(macneil near3 john).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 11:35
-	11	(beekman near3 knut).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 11:35
-	0	(wilby near3 anthony near3 paul).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 11:36
-	0	(wilby near3 anthony).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 11:36
-	0	(wilby near3 paul).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 11:36
-	32	((macneil near3 john).in.) ((beekman near3 knut).in.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 11:37
-	82	(trikon near3 holdings).as.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 11:37
-	102	((macneil near3 john).in.) ((beekman near3 knut).in.) ((trikon near3 holdings).as.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 11:37
-	18	((macneil near3 john).in.) ((beekman near3 knut).in.) ((trikon near3 holdings).as.) and (plasma corona discharge) and (heat\$3 anneal\$3 hot)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 12:44
-	2	"6544858"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 12:44
-	41	("5270267".pn. ((US-3223040-\$.DID. OR US-4793524-\$.DID. OR US-5095938-\$.DID. OR US-5098741-\$.DID. OR US-5195655-\$.DID. OR US-5273851-\$.DID. OR US-5314724-\$.DID. OR US-5356034-\$.DID. OR US-5494712-\$.DID. OR US-5534069-\$.DID. OR US-5593741-\$.DID.) (US-4894254-\$.DID. OR US-4822632-\$.DID. OR US-4096315-\$.DID.) 6028015.pn. (US-5876503-\$.DID. OR US-5620524-\$.DID. OR US-5641559-\$.DID. OR US-5730804-\$.DID.)) 5786039.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 14:28

-	5	((("5270267".pn. ((US-3223040-\$.DID. OR US-4793524-\$.DID. OR US-5095938-\$.DID. OR US-5098741-\$.DID. OR US-5195655-\$.DID. OR US-5273851-\$.DID. OR US-5314724-\$.DID. OR US-5356034-\$.DID. OR US-5494712-\$.DID. OR US-5534069-\$.DID. OR US-5593741-\$.DID.) (US-4894254-\$.DID. OR US-4822632-\$.DID. OR US-4096315-\$.DID.) 6028015.pn. (US-5876503-\$.DID. OR US-5620524-\$.DID. OR US-5641559-\$.DID. OR US-5730804-\$.DID.))) 5786039.pn.) and hydrogen near3 plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 14:29
-	8	((("5270267".pn. ((US-3223040-\$.DID. OR US-4793524-\$.DID. OR US-5095938-\$.DID. OR US-5098741-\$.DID. OR US-5195655-\$.DID. OR US-5273851-\$.DID. OR US-5314724-\$.DID. OR US-5356034-\$.DID. OR US-5494712-\$.DID. OR US-5534069-\$.DID. OR US-5593741-\$.DID.) (US-4894254-\$.DID. OR US-4822632-\$.DID. OR US-4096315-\$.DID.) 6028015.pn. (US-5876503-\$.DID. OR US-5620524-\$.DID. OR US-5641559-\$.DID. OR US-5730804-\$.DID.))) 5786039.pn.) and hydrogen near9 plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 14:29
-	80	(heat\$3 anneal\$3) near9 hydrogen near9 plasma and crack\$3 and semiconduct\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 14:31
-	3	(heat\$3 anneal\$3) same (CVD (chemical near3 vapo\$1r near3 deposit\$4)) same (silane organosilane organosilicon) same hydrogen near9 plasma and crack\$3 and semiconduct\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 14:33
-	83	(heat\$3 anneal\$3) same (CVD (chemical near3 vapo\$1r near3 deposit\$4)) same (silane organosilane organosilicon) same hydrogen near9 plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 14:34
-	8	(heat\$3 anneal\$3) same (CVD (chemical near3 vapo\$1r near3 deposit\$4)) same (silane organosilane organosilicon) same hydrogen near9 peroxide and hydrogen near9 plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 14:43
-	44	(heat\$3 anneal\$3) same (CVD (chemical near3 vapo\$1r near3 deposit\$4)) same (silane organosilane organosilicon) and hydrogen near9 peroxide and hydrogen near9 plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 15:08
-	4	(heat\$3 anneal\$3) same (CVD (chemical near3 vapo\$1r near3 deposit\$4)) same (organosilane organosilicon) and hydrogen near9 peroxide and hydrogen near9 plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 15:09
-	14	(heat\$3 anneal\$3) same (CVD (chemical near3 vapo\$1r near3 deposit\$4)) same (((methyl ethyl) near3 silane) organosilane organosilicon) and hydrogen near9 peroxide and hydrogen near9 plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 15:22
-	27	(heat\$3 anneal\$3) same (CVD (chemical near3 vapo\$1r near3 deposit\$4)) same (((methyl ethyl) near3 silane) organosilane organosilicon) and (carbon methyl) and hydrogen near9 plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 15:23
-	0	((heat\$3 anneal\$3) same (CVD (chemical near3 vapo\$1r near3 deposit\$4)) same (((methyl ethyl) near3 silane) organosilane organosilicon) and (carbon methyl) and hydrogen near9 plasma) not ((heat\$3 anneal\$3) same (CVD (chemical near3 vapo\$1r near3 deposit\$4)) same (((methyl ethyl) near3 silane) organosilane organosilicon) and carbon and hydrogen near9 plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 15:23

-	27	(heat\$3 anneal\$3) same (CVD (chemical near3 vapo\$1r near3 deposit\$4)) same (((methyl ethyl) near3 silane) organosilane organosilicon) and carbon and hydrogen near9 plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 16:44
-	5	"6383951"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 16:39
-	2	"6383951" and hydrogen near9 plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 16:40
-	14	"5593741" and hydrogen near9 plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 16:41
-	23	(heat\$3 anneal\$3) same (CVD (chemical near3 vapo\$1r near3 deposit\$4)) same (((methyl ethyl) near3 silane) organosilane organosilicon) and hydrogen near3 plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 16:52
-	124	"6054379"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 16:47
-	10	"6054379" and hydrogen near3 plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 16:48
-	79	crack\$3 same hydrogen near3 plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 16:50
-	14	(crack\$3 same hydrogen near3 plasma) and low near9 dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 16:49
-	55	low near2 "k" near3 dielectric same hydrogen near3 plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 16:52
-	28	low near2 "k" near3 dielectric and hydrogen near3 plasma and (CVD (chemical near3 vapo\$1r near3 deposit\$4)) same (((methyl ethyl) near3 silane) organo\$1silane organosilicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 17:02
-	24	hydrogen near3 plasma near9 (treat\$9 heat\$3 anneal\$3) and (CVD (chemical near3 vapo\$1r near3 deposit\$4)) same (((methyl ethyl) near3 silane) organo\$1silane organosilicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 16:56
-	237	hydrogen near3 plasma near9 (treat\$9 heat\$3 anneal\$3) and (CVD (chemical near3 vapo\$1r near3 deposit\$4)) same (((methyl ethyl) near3 silane) silane organo\$1silane organosilicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 16:56

-	25	hydrogen near3 plasma near9 (treat\$9 heat\$3 anneal\$3) same (CVD (chemical near3 vapo\$1r near3 deposit\$4)) same (((methyl ethyl) near3 silane) silane organo\$1silane organosilicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 17:07
-	361	hydrogen near3 plasma same (treat\$9 heat\$3 anneal\$3) and (CVD (chemical near3 vapo\$1r near3 deposit\$4)) same (methyl\$1silane silane organo\$1silane organosilicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 17:02
-	35	low near2 "k" near3 dielectric and (hydrogen near3 plasma same (treat\$9 heat\$3 anneal\$3) and (CVD (chemical near3 vapo\$1r near3 deposit\$4)) same (methyl\$1silane silane organo\$1silane organosilicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 17:02
-	1	hydrogen near3 plasma same flowfill	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 17:07
-	10	hydrogen near3 plasma and flowfill	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 17:10
-	206	hydrogen near3 plasma same (treat\$9 heat\$3 anneal\$4) same (flowfill "flowfill" (silicon near2 oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 17:11
-	221	hydrogen near3 plasma same (treat\$9 heat\$3 anneal\$4) same (flowfill "flowfill" (silicon near2 oxide) (low near2 "k" near3 dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 17:13
-	210	(hydrogen near3 plasma same (treat\$9 heat\$3 anneal\$4) same (flowfill "flowfill" (silicon near2 oxide) (low near2 "k" near3 dielectric))) not (low near2 "k" near3 dielectric and (hydrogen near3 plasma same (treat\$9 heat\$3 anneal\$3) and (CVD (chemical near3 vapo\$1r near3 deposit\$4)) same (methyl\$1silane silane organo\$1silane organosilicon)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 17:12
-	243	hydrogen near3 plasma same (treat\$9 heat\$3 anneal\$3) and (CVD (chemical near3 vapo\$1r near3 deposit\$4)) same (methyl\$1silane silane organo\$1silane organosilicon) and (flowfill "flowfill" (silicon near2 oxide) (low near2 "k" near3 dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 17:16
-	35	hydrogen near3 plasma same (treat\$9 heat\$3 anneal\$3) and (CVD (chemical near3 vapo\$1r near3 deposit\$4)) same (methyl\$1silane silane organo\$1silane organosilicon) and (flowfill "flowfill" (low near2 "k" near3 dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 17:15
-	0	(hydrogen near3 plasma same (treat\$9 heat\$3 anneal\$3) and (CVD (chemical near3 vapo\$1r near3 deposit\$4)) same (methyl\$1silane silane organo\$1silane organosilicon) and (flowfill "flowfill" (low near2 "k" near3 dielectric))) not (low near2 "k" near3 dielectric and (hydrogen near3 plasma same (treat\$9 heat\$3 anneal\$3) and (CVD (chemical near3 vapo\$1r near3 deposit\$4)) same (methyl\$1silane silane organo\$1silane organosilicon)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 17:15
-	996	hydrogen near3 plasma same (treat\$9 heat\$3 anneal\$3) and (CVD (chemical near3 vapo\$1r near3 deposit\$4)) same (methyl\$1silane silane organo\$1silane organosilicon flowfill "flowfill" (silicon near2 oxide) (low near2 "k" near3 dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 17:17

-	109	hydrogen near3 plasma same (treat\$9 heat\$3 anneal\$3) same (CVD (chemical near3 vapo\$1r near3 deposit\$4)) same (methyl\$1silane silane organo\$1silane organosilicon flowfill "flowfill" (silicon near2 oxide) (low near2 "k" near3 dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 17:17
-	100	(hydrogen near3 plasma same (treat\$9 heat\$3 anneal\$3) same (CVD (chemical near3 vapo\$1r near3 deposit\$4)) same (methyl\$1silane silane organo\$1silane organosilicon flowfill "flowfill" (silicon near2 oxide) (low near2 "k" near3 dielectric))) not (low near2 "k" near3 dielectric and (hydrogen near3 plasma same (treat\$9 heat\$3 anneal\$3) and (CVD (chemical near3 vapo\$1r near3 deposit\$4)) same (methyl\$1silane silane organo\$1silane organosilicon)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 19:09
-	2314	teos near3 tetraethoxy\$1silane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 18:03
-	146	(teos near3 tetraethoxy\$1silane).ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 18:03
-	20	"6063654"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 19:09